

ABSTRACT

The present invention relates to a manufacturing method for a semiconductor device that includes, at least, the step of forming a drift region of a second conductivity type provided with a low concentration region in the semiconductor substrate on, at least, one side in the channel length direction of the gate electrode by means of impurity ion implantations with predetermined implantation angles with four different directions; and the step of forming a high concentration region of the second conductivity type surrounded by the drift region, with the exception of the low concentration region.

A semiconductor device having a drift region that can be miniaturized without increase in the number of manufacturing steps as well as a manufacturing method for the same can be provided according to the above described method.